

SOT-23 Plastic-Encapsulate MOSFETS

Features

- $V_{DS} = -60V$
- $I_D = -1.25A$
- $R_{DS(on)}@V_{GS} = -10V < 340m\Omega$
- $R_{DS(on)}@V_{GS} = -4.5V < 550m\Omega$
- Trench Power MV MOSFET technology
- Voltage controlled small signal switch
- Fast Switching Speed

Applications

- Battery operated systems
- Solid-state relays
- Direct logic-level interface: TTL/CMOS

Mechanical Data

- Case: SOT-23
Molding compound meets UL 94V-0 flammability rating, RoHS-compliant, halogen-free
- Terminals: Solder plated, solderable per MIL-STD-750, Method 2026

Reference News

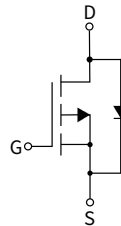
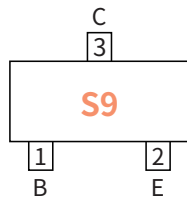
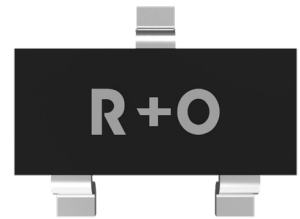
Drain-source Voltage

-60 V

Drain Current

-1.25 Ampere

SOT-23



Maximum Ratings (Ta=25°C Unless otherwise specified)

PARAMETER		SYMBOL	UNIT	VALUE
Drain-source Voltage		V_{DS}	V	-60
Gate-source Voltage		V_{GS}	V	± 20
Drain Current ⁽¹⁾⁽²⁾	$T_A = 25^\circ C$ @ Steady State	I_D	A	-1.25
	$T_A = 70^\circ C$ @ Steady State			-0.85
Pulsed Drain Current ⁽¹⁾⁽²⁾		I_{DM}	A	-8.0
Total Power Dissipation @ $T_A = 25^\circ C$		P_D	W	1.25
Thermal Resistance Junction-to-Ambient @ Steady State		$R_{\theta JA}$	$^\circ C / W$	357
Junction and Storage Temperature Range		T_J, T_{STG}	$^\circ C$	-55 ~ +150

Note:

(1) Surface Mounted on FR4 Board.

(2) $t \leq 5$ sec.

Ordering Information

PACKAGE	PACKAGE CODE	UNIT WEIGHT(g)	REEL(pcs)	BOX(pcs)	CARTON(pcs)	DELIVERY MODE
SOT-23	R1	0.008	3000	30000	120000	7"

● **Static Parameter Characteristics** (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	Condition	UNIT	Min	Typ	Max
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	V	-60	—	—
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-48V, V_{GS}=0V$	μA	—	—	-1.0
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	nA	—	—	± 100
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	V	-1.0	—	-3.0
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-1.25A$	m Ω	—	275	340
		$V_{GS}=-4.5V, I_D=-1.0A$		—	406	550
Forward Transconductance	g_{fs}	$V_{DS}=-4.5V, I_D=-1.0A$	S	—	1.9	—
Diode Forward Voltage	V_{SD}	$I_S=-1.25A, V_{GS}=0V$	V	—	-0.82	-1.2
Maximum Body-Diode Continuous Current	I_S	—	A	—	—	-1.25

● **Dynamic Parameters** (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	Condition	UNIT	Min	Typ	Max
Input Capacitance	C_{iss}	$V_{DS}=-30V$ $V_{GS}=0V$ $f=1MHz$	pF	—	380	—
Output Capacitance	C_{oss}			—	32	—
Reverse Transfer Capacitance	C_{rss}			—	6.0	—

● **Switching Parameters** (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	Condition	UNIT	Min	Typ	Max
Total Gate Charge	Q_g	$V_{GS}=-10V$ $V_{DS}=-30V$ $I_D=-1.25A$	nC	—	5.4	12
Gate-Source Charge	Q_{gs}			—	1.15	—
Gate-Drain Charge	Q_{gd}			—	0.92	—
Reverse Recovery Time	t_{rr}	$I_F=-1.25A, di/dt=100A/\mu s$	ns	—	30	55
Turn-on Delay Time	$t_{D(on)}$	$V_{GS}=-4.5V, V_{DS}=-30V$ $R_L=3.0\Omega, R_{GEN}=6.0\Omega$ $I_D=-1.0A$		—	10.5	20
Turn-on Rise Time	t_r			—	11.5	20
Turn-off Delay Time	$t_{D(off)}$			—	15.5	30
Turn-off fall Time	t_f			—	7.5	15

● Ratings And Characteristics Curves (Ta=25°C Unless otherwise specified)

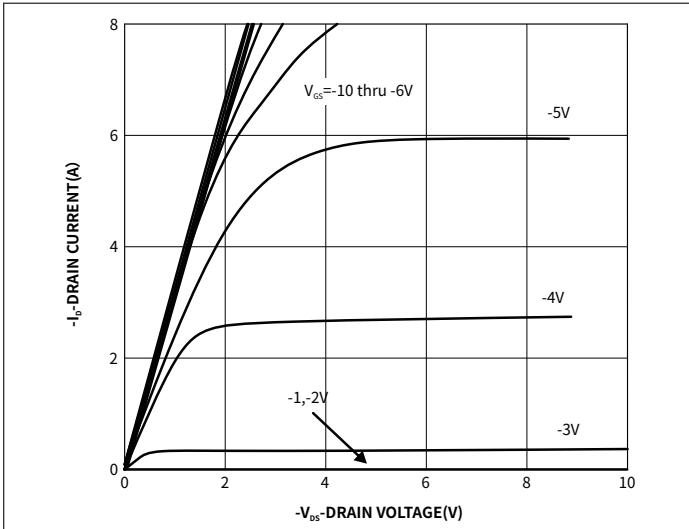


Fig.1 Output Characteristics

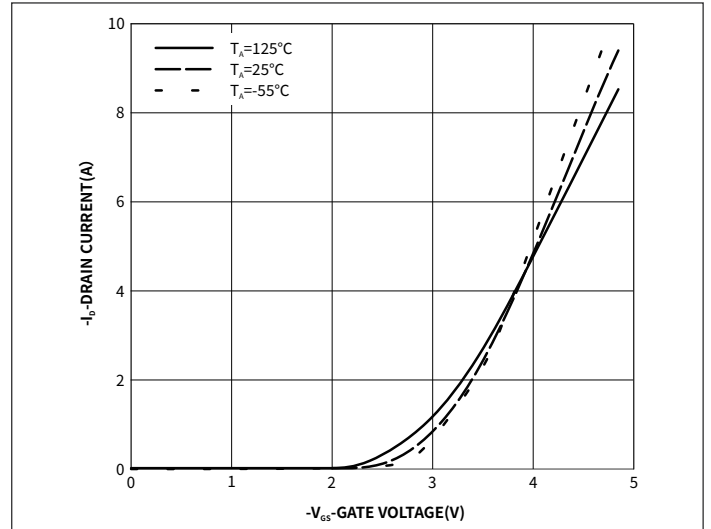


Fig.2 Transfer Characteristics

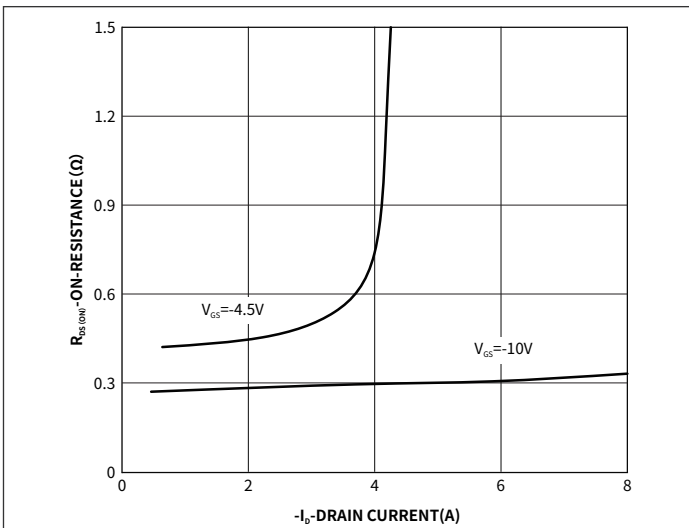


Fig.3 On-Resistance vs. Drain Current and Gate Voltage

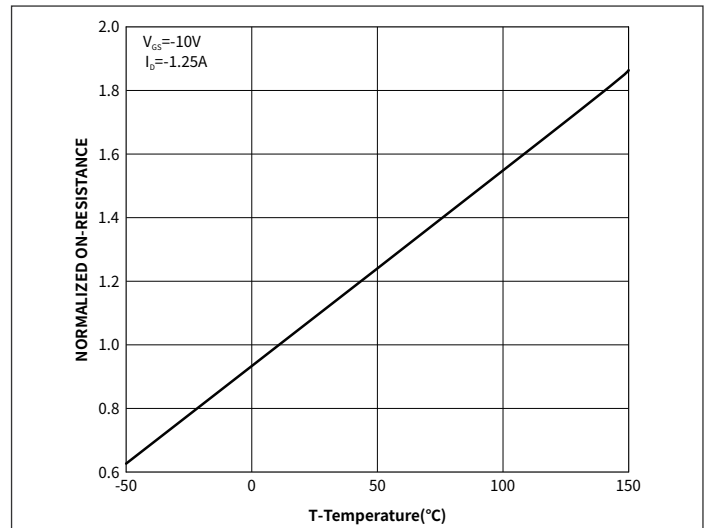


Fig.4 On-Resistance vs. Junction Temperature

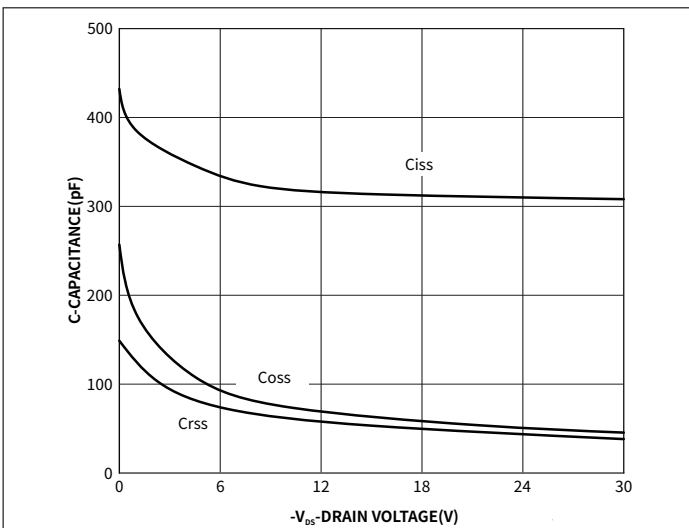


Fig.5 Capacitance Characteristics

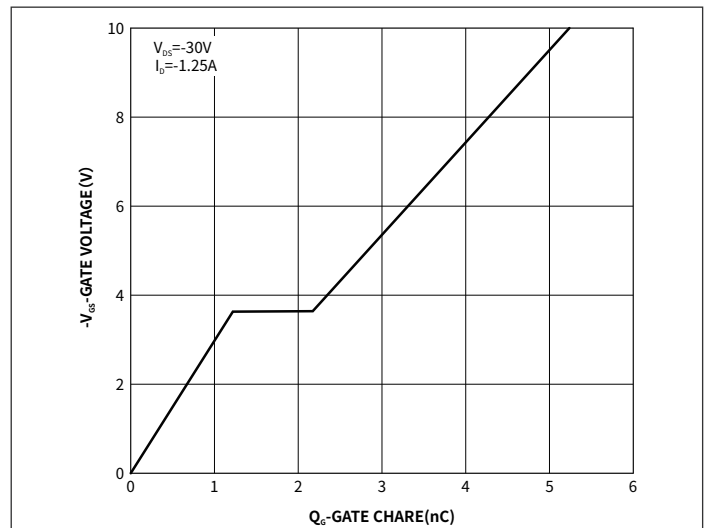
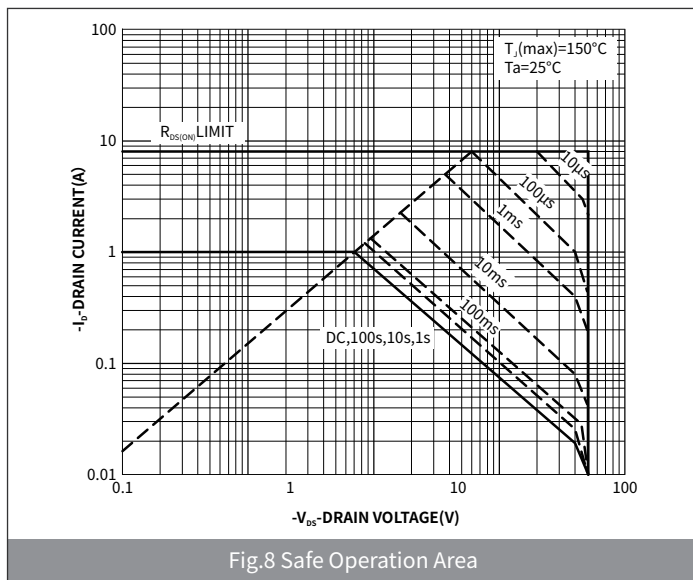
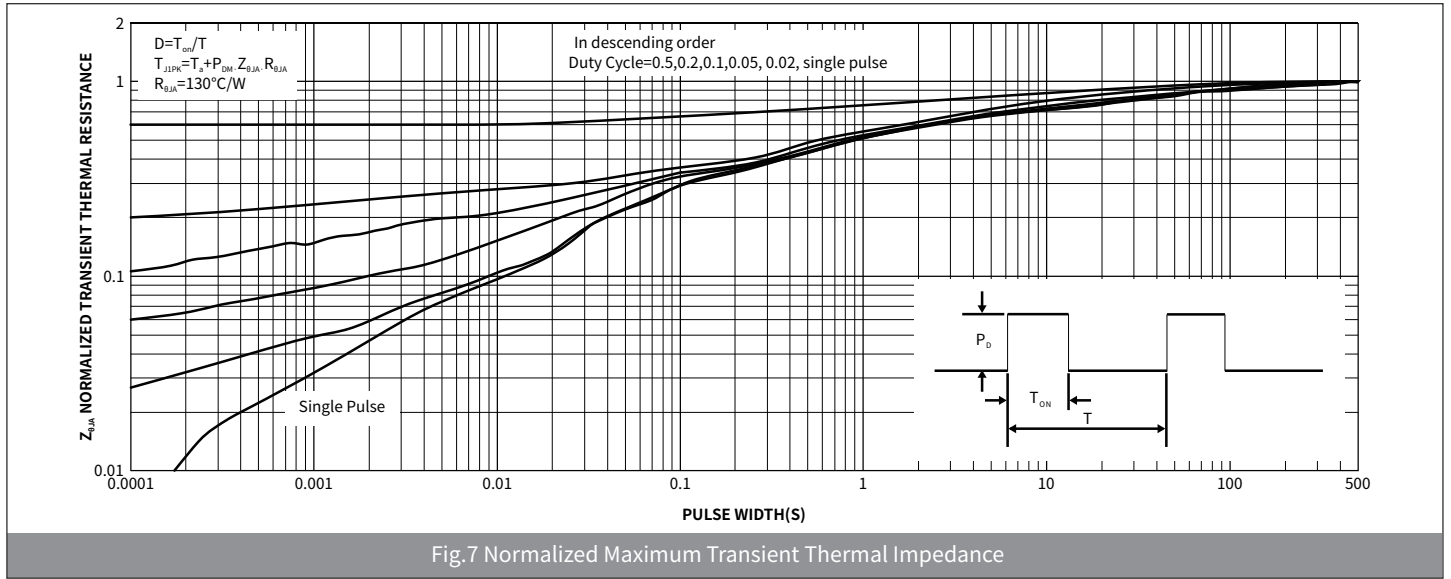


Fig.6 Gate Charge

● Ratings And Characteristics Curves (Ta=25°C Unless otherwise specified)



● Package Outline Dimensions (SOT-23)

Symbol	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	0.90	1.15	0.035	0.045
A1	-	0.10	-	0.004
A2	0.90	1.05	0.035	0.041
b	0.30	0.50	0.012	0.020
c	0.10	0.20	0.004	0.008
D	2.80	3.00	0.110	0.118
E	1.20	1.40	0.047	0.055
E1	2.25	2.55	0.089	0.100
e	0.950TYP		0.037TYP	
e1	1.80	2.00	0.071	0.079
L	0.550REF		0.022REF	
L1	0.30	0.50	0.012	0.020
θ	-	8°	-	8°

● Suggested Pad Layout

Symbol	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
J	0.80	-	0.031	-
K	-	0.90	-	0.035
M	2.00	-	0.078	-
N	-	1.90	-	0.074